

CDSH3-4448/A/C/S-G

Voltage: 80 Volts

Current: 250 mA

RoHS Device

Features

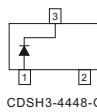
- Fast switching speed.
- For general purpose switching applications.
- High conductance.



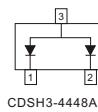
Mechanical data

- Case: SOT-523, molded plastic.
- Terminals: Solder plated, solderable per MIL-STD-202E, method 208C.
- Weight: 0.002 grams approx.

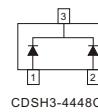
Circuit Diagram



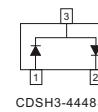
CDSH3-4448-G
Marking: A3



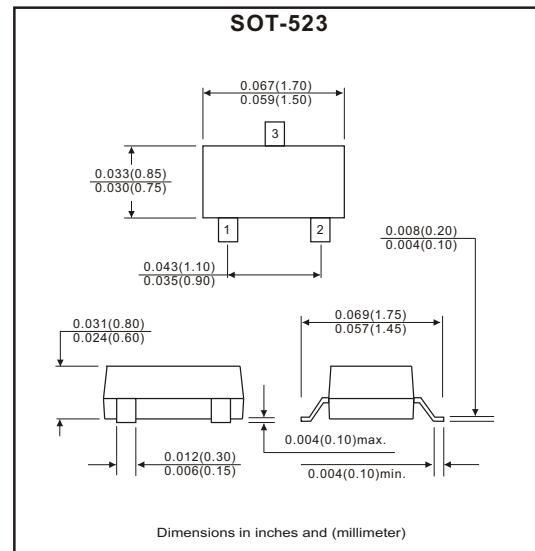
CDSH3-4448A-G
Marking: A6



CDSH3-4448C-G
Marking: A7



CDSH3-4448-S-G
Marking: AB



Maximum Ratings and Electrical Characteristics

(Single diode, at TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Non-repetitive peak reverse voltage	V _{RM}	100	V
Peak repetitive peak reverse voltage	V _{R_{RM}}		
Working peak reverse voltage	V _{R_{WM}}	80	V
DC blocking voltage	V _R		
RMS reverse voltage	V _{R(RMS)}	57	V
Forward continuous current	I _{FM}	500	mA
Averaged rectified output current	I _O	250	mA
Peak forward surge current @TP=1.0μS @TP=1.0S	I _{FSM}	4.0 2.0	A
Power dissipation	P _D	150	mW
Thermal resistance, junction to ambient	R _{θJA}	833	°C/W
Storage temperature	T _{STG}	-65 to +150	°C

Electrical Ratings @TA=25°C

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Reverse breakdown voltage	V _{BR}	I _R =2.5μA	80			V
Forward voltage	V _{F1}	I _F =5mA	0.62		0.72	V
	V _{F2}	I _F =10mA			0.855	V
	V _{F3}	I _F =100mA			1.0	V
	V _{F4}	I _F =150mA			1.25	V
Reverse current	I _{R1}	V _R =70V			0.1	μA
	I _{R2}	V _R =20V			25	nA
Capacitance between terminals	C _T	V _R =6V, f=1MHz			3.5	pF
Reverse recovery time	T _{rr}	V _R =6V, I _f =5mA			4	nS

REV:A

SMD Switching Diodes

COMCHIP
SMD Diodes Specialist

Rating and Characteristic Curves (CDSH3-4448/A/C/S-G)

Fig.1 Forward Characteristics

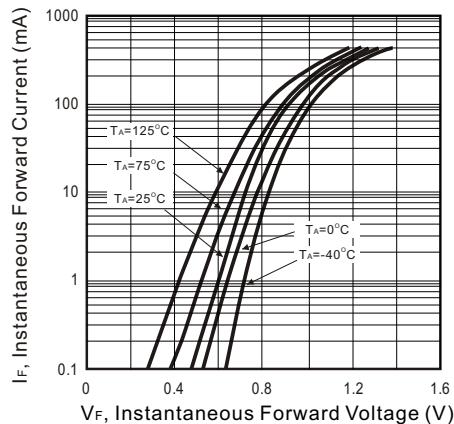


Fig.2 Reverse Characteristics

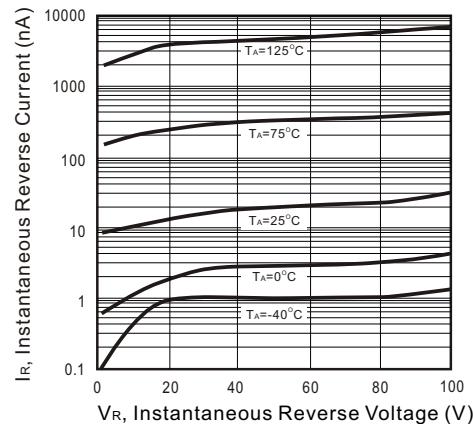


Fig.3 Capacitance Between Terminals Characteristics

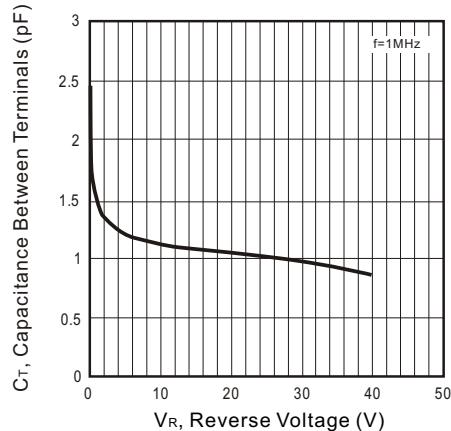


Fig.4 Power Derating Curve

